
2SJ548

Silicon P Channel MOS FET
High Speed Power Switching

HITACHI

ADE-208-639A (Z)

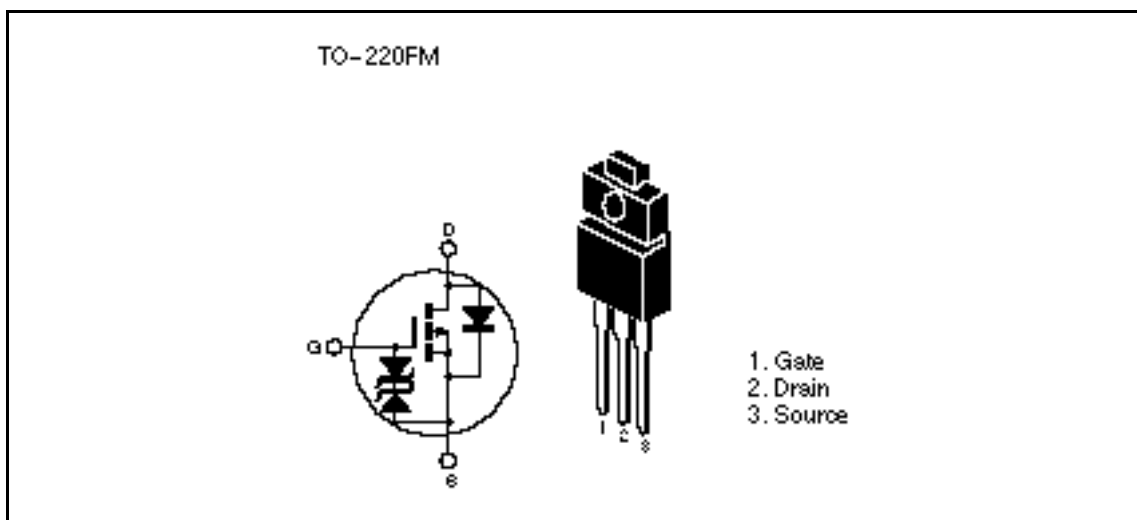
2nd. Edition

Jun 1998

Features

- Low on-resistance
 $R_{DS(on)} = 0.075 \text{ typ.}$
- Low drive current.
- 4V gate drive devices.
- High speed switching.

Outline



2SJ548

Absolute Maximum Ratings (Ta = 25°C)

| Item | Symbol | Ratings | Unit |
|--|---------------------------------|-------------|------|
| Drain to source voltage | V_{DSS} | -60 | V |
| Gate to source voltage | V_{GSS} | ± 20 | V |
| Drain current | I_D | -15 | A |
| Drain peak current | $I_{D(pulse)}$ ^{Note1} | -60 | A |
| Body-drain diode reverse drain current | I_{DR} | -15 | A |
| Avalanche current | I_{AP} ^{Note3} | -15 | A |
| Avalanche energy | E_{AR} ^{Note3} | 19 | mJ |
| Channel dissipation | P_{ch} ^{Note2} | 30 | W |
| Channel temperature | T_{ch} | 150 | °C |
| Storage temperature | T_{stg} | -55 to +150 | °C |

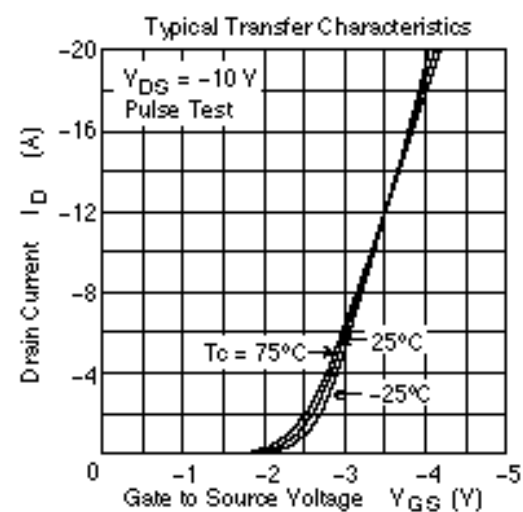
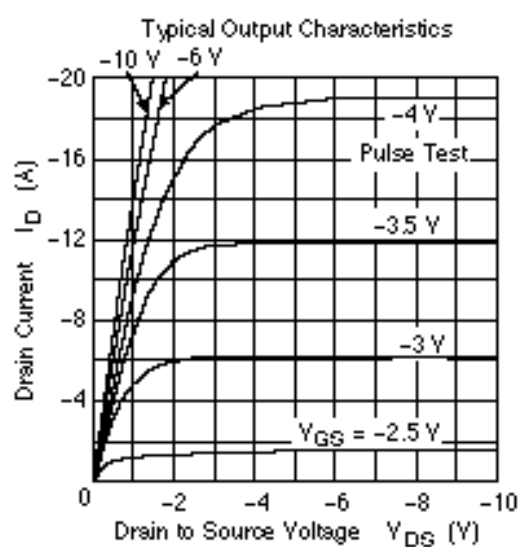
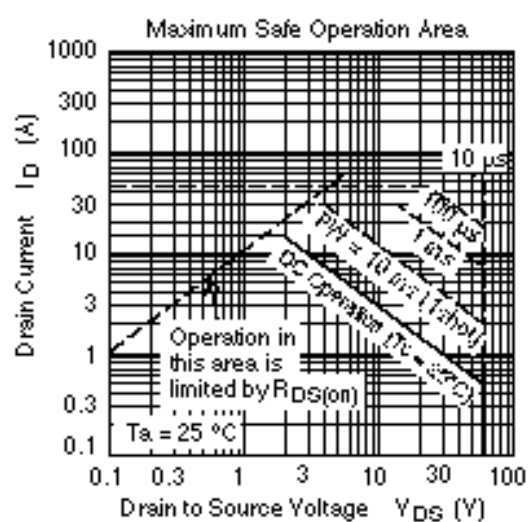
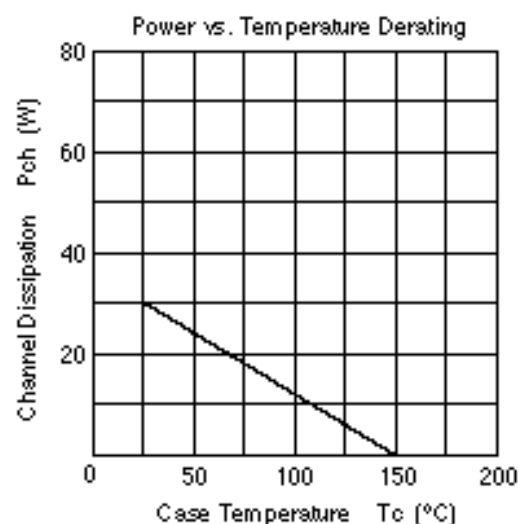
Note: 1. PW 10μs, duty cycle 1 %
 2. Value at Tc = 25°C
 3. Value at Tch = 25°C, Rg 50

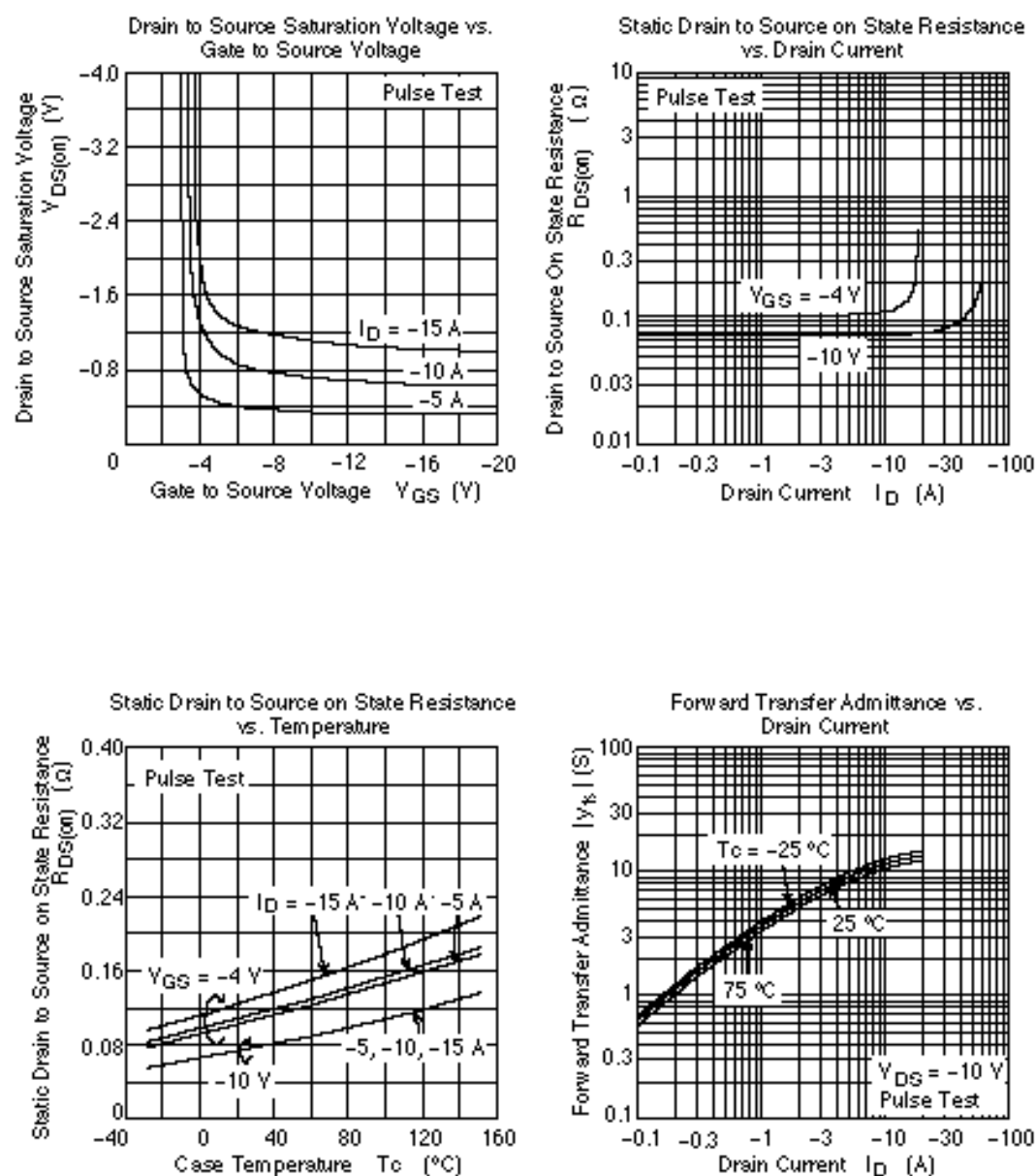
Electrical Characteristics (Ta = 25°C)

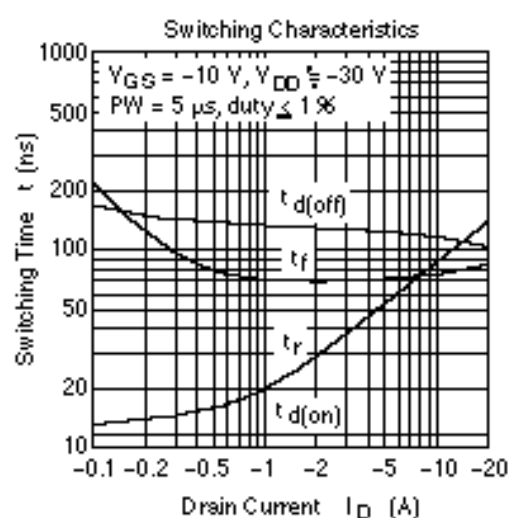
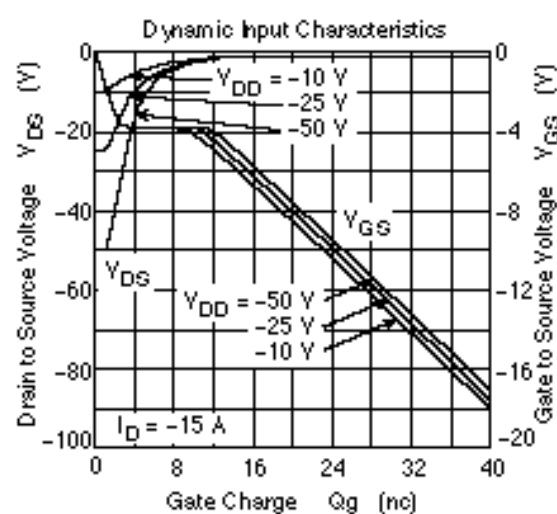
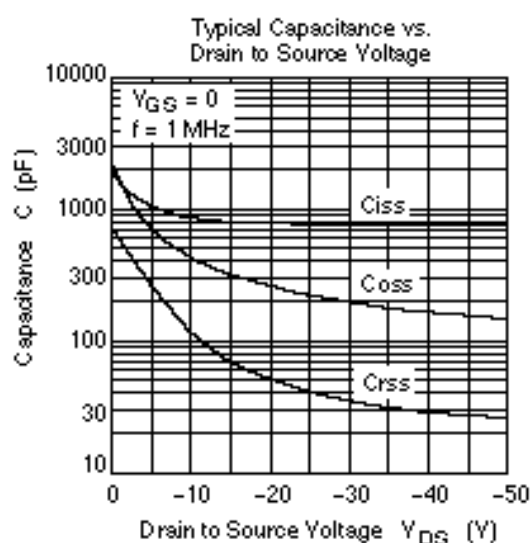
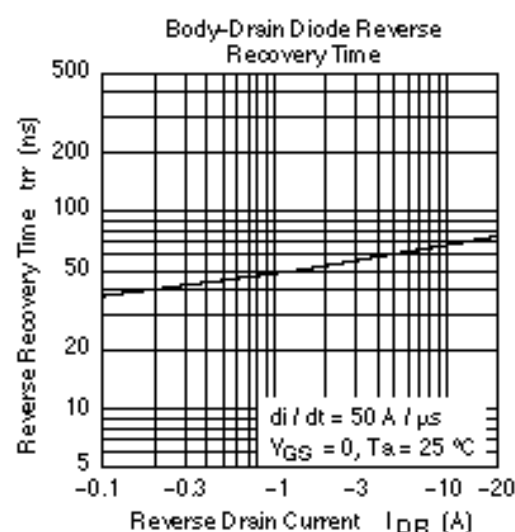
| Item | Symbol | Min | Typ | Max | Unit | Test Conditions |
|--|---------------|----------|-------|----------|------|--|
| Drain to source breakdown voltage | $V_{(BR)DSS}$ | -60 | — | — | V | $I_D = -10mA, V_{GS} = 0$ |
| Gate to source breakdown voltage | $V_{(BR)GSS}$ | ± 20 | — | — | V | $I_G = \pm 100\mu A, V_{DS} = 0$ |
| Zero gate voltage drain current | I_{DSS} | — | — | -10 | μA | $V_{DS} = -60V, V_{GS} = 0$ |
| Gate to source leak current | I_{GSS} | — | — | ± 10 | μA | $V_{GS} = \pm 16V, V_{DS} = 0$ |
| Gate to source cutoff voltage | $V_{GS(off)}$ | -1.0 | — | -2.0 | V | $I_D = -1mA, V_{DS} = -10V$ |
| Static drain to source on state resistance | $R_{DS(on)}$ | — | 0.075 | 0.095 | | $I_D = -8A, V_{GS} = -10V$ ^{Note4} |
| | $R_{DS(on)}$ | — | 0.105 | 0.155 | | $I_D = -8A, V_{GS} = -4V$ ^{Note4} |
| Forward transfer admittance | $ y_{fs} $ | 6.5 | 11 | — | S | $I_D = -8A, V_{DS} = -10V$ ^{Note4} |
| Input capacitance | C_{iss} | — | 850 | — | pF | $V_{DS} = -10V$ |
| Output capacitance | C_{oss} | — | 420 | — | pF | $V_{GS} = 0$ |
| Reverse transfer capacitance | C_{rss} | — | 110 | — | pF | $f = 1MHz$ |
| Turn-on delay time | $t_{d(on)}$ | — | 12 | — | ns | $V_{GS} = -10V, I_D = -8A$ |
| Rise time | t_r | — | 75 | — | ns | $R_L = 3.75$ |
| Turn-off delay time | $t_{d(off)}$ | — | 125 | — | ns | |
| Fall time | t_f | — | 75 | — | ns | |
| Body-drain diode forward voltage | V_{DF} | — | -1.1 | — | V | $I_F = -15A, V_{GS} = 0$ |
| Body-drain diode reverse recovery time | t_{rr} | — | 70 | — | ns | $I_F = -15A, V_{GS} = 0$ $diF/dt = 50A/\mu s$ |

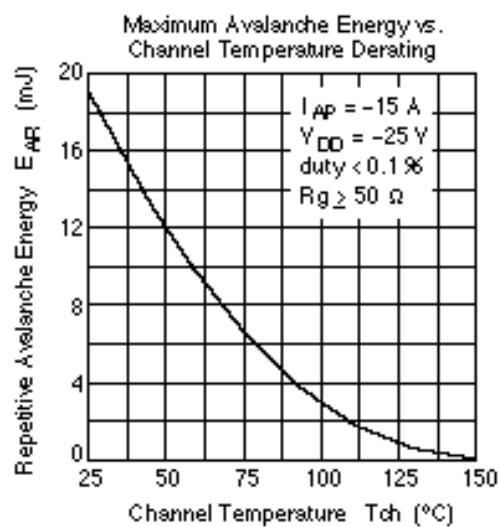
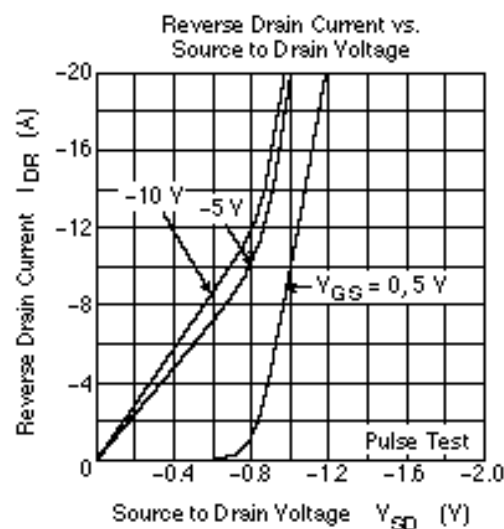
Note: 4. Pulse test

Main Characteristics

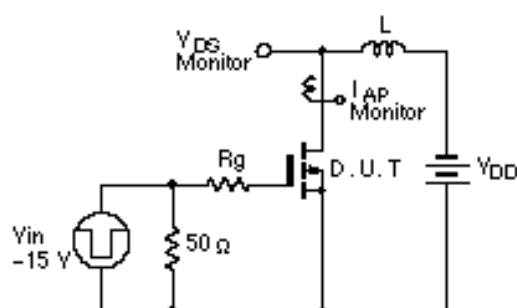




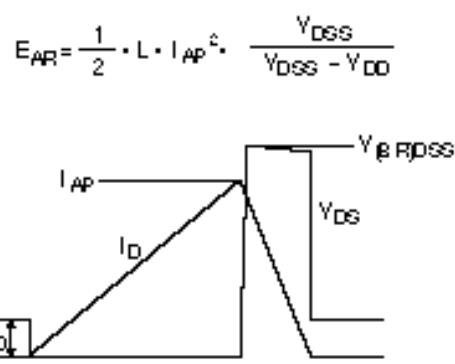


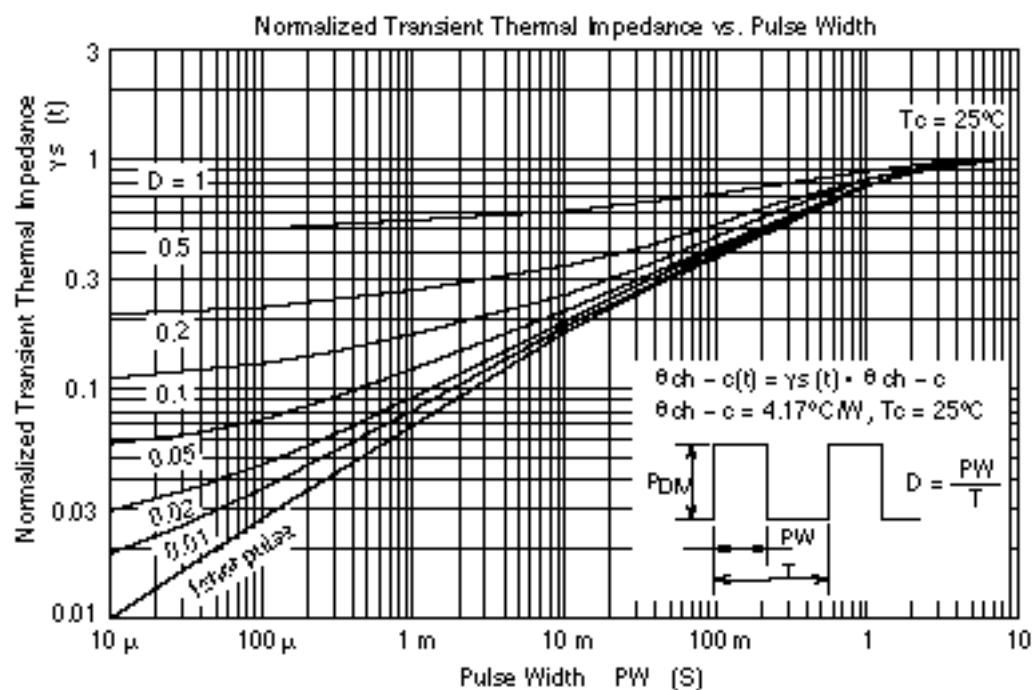


Avalanche Test Circuit

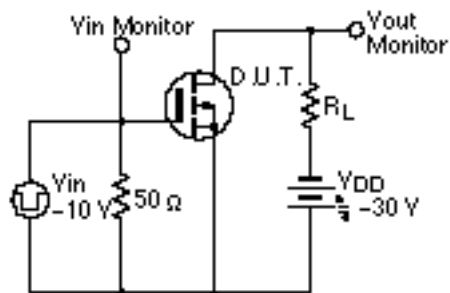


Avalanche Waveform

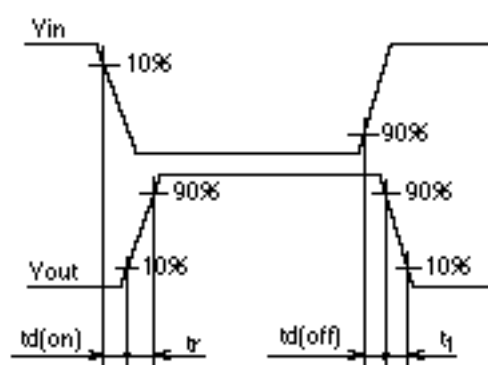




Switching Time Test Circuit



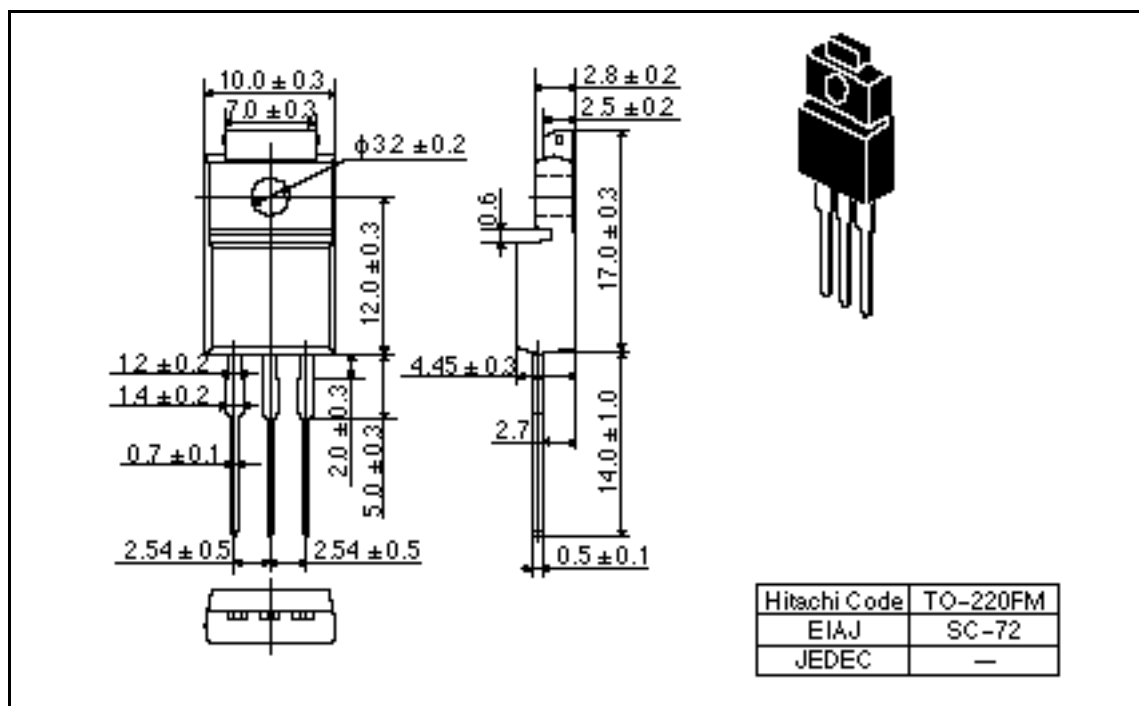
Waveform



2SJ548

Package Dimensions

Unit: mm



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